

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	JP-2004111936-\$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/01 17:45
S2	4	("2002049117").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/10/01 17:52
S3	2	("20020049117").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/10/01 17:53
S4	2	("20020149117").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/10/01 17:53
S5	7	(chip-on-chip or coc) and electrode same (low near5 melt\$3 near5 layer) and board and (SnIn or In or bi or Snbi) same thickness	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/01 18:00
S6	4	(chip-on-chip or coc) and electrode same (low near5 melt\$3 near5 layer) and board and (SnIn or indium or bismuth or bi or Snbi) same thickness	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/01 18:01
S7	5	("5611481").PN. OR ("6734556").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/01 18:03
S8	27	("5611481").URPN.	USPAT	OR	ON	2008/10/01 18:08
S9	1	S8 and electrode same (low near5 melt\$3 near5 layer) and board and (SnIn or indium or bismuth or bi or Snbi) same thickness	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/01 18:11

S10	6	("5611481" "5808853" "6550665" "6569752" "6818996" "6882045"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/01 18:12
S11	4	(S8 or S10) and electrode same (low near5 melt\$3 near5 layer) and board and thickness	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/01 18:12
S12	0	228/194.ccls. and electrode same (low near5 melt\$3 near5 layer) and board	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/01 18:14
S13	0	228/194.ccls. and (bump or electrode) same (low near5 melt\$3 near5 layer) and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/01 18:15
S14	16	"228".clas. and (bump or electrode) same (low near5 melt\$3 near5 layer) and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/01 18:15
S15	50	(bump or electrode) same (low near5 melt\$3 near5 layer) and semiconductor and roughness	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/02 08:18
S16	46	(bump or electrode) same (low near5 melt\$3 near5 layer) and semiconductor and surface near5 roughness	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/02 08:19
S17	33	S16 and @ad< "20040302"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/02 08:19
S18	14	S17 and vapor near5 deposit\$4 and evaporat\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/02 08:19

S19	26	us-4746055-\$.did. or us-20020006685-\$.did. or EP-966038-\$.did. or de-4303790-\$.did. or JP-1997036186-\$.did. or jp-2002110726-\$.did. or jp-2003302065-\$.did. or jp-2001274195-\$.did. or jp-2003084436-\$.did. or jp-1992089211-\$.did. or jp-1993009713-\$.did. or jp-2002043348-\$.did. or jp-2004111936-\$.did. or jp-2002289768-\$.did. or jp-2001274201-\$.did. or jp-2004111935-\$.did. or jp-1998256319-\$.did. or jp-1993074824-\$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/02 08:49
S20	4	(("6551854") or ("6583514")).FN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/10/02 09:05
S21	2	("20020090756").FN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/10/02 09:53
S22	1	(bump or electrode) same (low near5 melt\$3 near5 layer) and semiconductor and plating near5 roughness	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/02 11:13
S23	7	(bump or electrode) same (low near5 melt\$3 near5 layer) and semiconductor and plating same roughness	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/02 11:14
S24	3	(bump or electrode) same (low near5 melt\$3 near5 layer) and semiconductor and (bond\$3 or join\$3) near10 roughness	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/02 11:17

S25	2	electrode same ((bond\$3 or join\$3) near10 roughness) and (low near5 melt\$3 near5 layer) and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/02 11:20
S26	6	electrode same ((bond\$3 or join\$3) same roughness) and (low near5 melt\$3 near5 layer) and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/02 11:20
S27	19	electrode same ((bond\$3 or join\$3) same roughness) and board same chip same semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/02 11:22
S28	16	"6002173"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/02 11:26
S29	2	("5794839").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/10/02 11:31

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